

ABSTRACT OF THE DISCLOSURE

A method of designing an MOSFET of the present invention is concerned with design of a photomask which is used in a patterning process for forming an element isolation insulating film. An element forming region includes in top view a projecting portion (8a, 8b) along its perimeter. With respect to the structure in which the projecting portion (8a, 8b) is not provided, stress exerted on a semiconductor substrate (1) from an element isolation insulating film (2) varies. Provision of the projecting portion (8a, 8b) thus allows fine control of stress exerted on an area of the semiconductor substrate (1) holding a gate structure (3) thereover. As a result, the current driving capability of an MOSFET can be controlled at a desirable level.